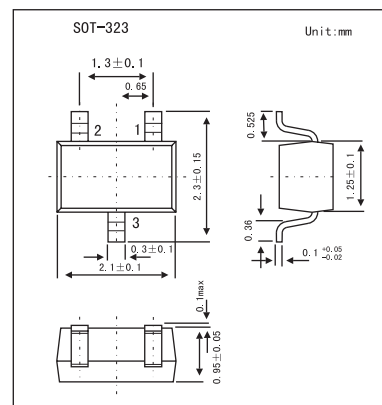


Silicon Schottky Diodes

BAT68W

■ Features

- For mixer applications in the VHF/UHF range
- For high speed switching

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	8	V
Forward current	I_F	150	mA
Total power dissipation $T_s = 97^\circ\text{C}$	P_{tot}	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Operating temperature range	T_{op}	-65 to +150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction - ambient (Note 1)	R_{thJA}	≤ 435	K/W
Junction - soldering point	R_{thJS}	≤ 355	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	$I_{(BR)} = 100 \mu\text{A}$	8			V
Reverse current	I_R	$V_R = 1 \text{ V}, T_A = 25^\circ\text{C}$			0.1	μA
		$V_R = 1 \text{ V}, T_A = 60^\circ\text{C}$			1.2	
Forward voltage	V_F	$I_F = 1 \text{ mA}$		318	340	mV
		$I_F = 10 \text{ mA}$	340	390	500	
Diode capacitance	C_T	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$			1	pF
Differential forward resistance	R_F	$I_F = 5 \text{ mA}$			10	Ω

■ Marking

Marking	83s
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